





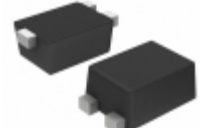



	<h2>NSBC123JPDXV6T1G</h2>
	<p>Hersteller-Teilenummer: NSBC123JPDXV6T1G</p> <p>Hersteller / Marke: AMI Semiconductor / ON Semiconductor</p> <p>Teil der Beschreibung: TRANS PREBIAS NPN/PNP SOT563</p> <p>Datenblätter:  NSBC123JPDXV6T1G.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 16000 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
	
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	NSBC123JPDXV6T1G
Hersteller	AMI Semiconductor / ON Semiconductor
Beschreibung	TRANS PREBIAS NPN/PNP SOT563
Kategorie	Diskrete Halbleiterprodukte > Transistoren-bipolare
Teilstatus	16000 pcs Stock
Serie	-
Befestigungsart	Surface Mount
Leistung - max	500mW
Verpackung / Gehäuse	SOT-563, SOT-666
Supplier Device-Gehäuse	SOT-563
Transistor-Typ	1 NPN, 1 PNP - Pre-Biased (Dual)
Strom - Kollektor (Ic) (max)	100mA
Spannung - Kollektor-Emitter-Durchbruch (max)	50V
VCE Sättigung (Max) @ Ib, Ic	250mV @ 300µA, 10mA
Strom - Collector Cutoff (Max)	500nA
DC Stromgewinn (HFE) (Min) @ Ic, VCE	80 @ 5mA, 10V
Frequenz - Übergang	-
Widerstand - Base (R1) (Ohm)	2.2k
Widerstand - Emitter-Basis (R2) (Ohm)	47k
Verpackung	Tape & Reel (TR)
















NSBC123JPDXV6T1G ist neu im Original. Suche NSBC123JPDXV6T1G Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie NSBC123JPDXV6T1G AMI Semiconductor / ON Semiconductor mit Garantie und Vertrauen. Anfrage NSBC123JPDXV6T1G: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>NSBC123TPDP6T5G AMI Semiconductor / ON Semiconductor TRANS PREBIAS NPN 254MW SOT963</p>	 <p>NSBC123JPDXV6T1 AMI Semiconductor / ON Semiconductor TRANS PREBIAS NPN/PNP SOT563</p>	 <p>NSBC124EDP6T5G AMI Semiconductor / ON Semiconductor TRANS 2NPN PREBIAS 0.339W SOT963</p>	 <p>NSBC123TDP6T5G AMI Semiconductor / ON Semiconductor TRANS 2NPN PREBIAS 0.339W SOT963</p>
 <p>NSBC123TF3T5G AMI Semiconductor / ON Semiconductor TRANS PREBIAS NPN 254MW SOT1123</p>	 <p>NSBC123JDXV6T5 AMI Semiconductor / ON Semiconductor TRANS 2NPN PREBIAS 0.5W SOT563</p>	 <p>NSBC123JPDP6T5G AMI Semiconductor / ON Semiconductor TRANS 2NPN PREBIAS 0.339W SOT963</p>	 <p>NSBC123JDXV6T1 AMI Semiconductor / ON Semiconductor TRANS 2NPN PREBIAS 0.5W SOT563</p>

heiße Teile

Mehr

 E157654FOOA	 GM66102-12TB3T	 KLM-R-20	 L6730TR-9LF	 LM-220-CW
 LT2079IS	 NSB1706DMW5T1G	 NSB4904DW1T1G	 NSB8JT-E3/31	 NSB9435T1
 NSB9435T1G	 NSBA114EDP6T5G	 NSBA114EDXV6T1	 NSBA114YDXV6T1	 NSBA123JDXV6T1
 NSBA123JDXV6T1G	 NSBA123JDXV6T5G	 NSBA143TDXV6T1G	 NSBA144EDP6T5G	 NSBC114EDXV6T1
 NSBC114EDXV6T1G	 NSBC114EPDXV6T1G	 NSBC114EPDXV6T5	 NSBC114TDXV6T1	 NSBC114YDP6T5G
 NSBC114YDXV6T1	 NSBC114YDXV6T1G	 NSBC114YDXV6T5	 NSBC114YDPDXV6T1	 NSBC115EDXV6T1
 NSBC123JDXV6T1	 NSBC123JPDXV6T1	 NSBC124EPDXV6T1	 NSBC124EPDXV6T5	 NSBC124XPDXV6T1
 NSBC143EDXV6T5	 NSBC143ZPDXV6T1G	 NSBC143ZPDXV6T5	 NSBC144EDXV6T1	 NSBC144EDXV6T1G
 NSBC144EDXV6T5	 NSBC144EDXV6T5G	 NSBC144EPDXV6T1	 NSBC144EPDXV6T1G	 RB521CM-30T2R
 S-8261BAL-M6T1U	 SKR2M240/18	 SN74F08N	 TM60DZ-M	 W0428RE32

Contact us: Info@Y-IC.com

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